

ABSTRACT

Abrasive composition for the chemical-mechanical polishing in one stage of substrates used in the microelectronics semiconductors industry containing at least one metal
5 layer and one insulator layer, comprising an acid aqueous suspension of individualized particles of colloidal silica, not linked to each other by siloxane bonds, having a mean particle diameter of between 5 and 20 nm and an oxidizing agent, and chemical-mechanical polishing process using such a composition.